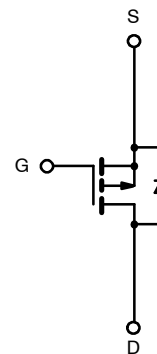
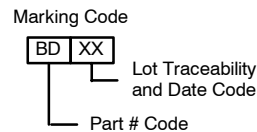
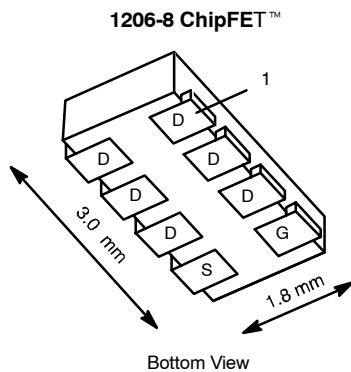


## P-Channel 20-V (D-S) MOSFET

<b>PRODUCT SUMMARY</b>		
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
-20	0.040 @ $V_{GS} = -4.5$ V	-6.7
	0.052 @ $V_{GS} = -2.5$ V	-5.9
	0.072 @ $V_{GS} = -1.8$ V	-5.0

**TrenchFET®**  
Power MOSFETs  
1.8-V Rated



P-Channel MOSFET

Ordering Information: Si5433DC-T1

<b>ABSOLUTE MAXIMUM RATINGS (<math>T_A = 25^\circ\text{C}</math> UNLESS OTHERWISE NOTED)</b>					
Parameter		Symbol	5 secs	Steady State	Unit
Drain-Source Voltage		$V_{DS}$	-20		V
Gate-Source Voltage		$V_{GS}$	$\pm 8$		
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ ) <sup>a</sup>	$T_A = 25^\circ\text{C}$	$I_D$	-6.7	-4.8	A
	$T_A = 85^\circ\text{C}$		-4.8	-3.5	
Pulsed Drain Current		$I_{DM}$	-20		
Continuous Source Current <sup>a</sup>		$I_S$	-2.1	-1.1	
Maximum Power Dissipation <sup>a</sup>	$T_A = 25^\circ\text{C}$	$P_D$	2.5	1.3	W
	$T_A = 85^\circ\text{C}$		1.3	0.7	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 150		$^\circ\text{C}$
Soldering Recommendations (Peak Temperature) <sup>b, c</sup>			260		

<b>THERMAL RESISTANCE RATINGS</b>					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$t \leq 5$ sec	$R_{thJA}$	40	50	$^\circ\text{C}/\text{W}$
	Steady State		80	95	
Maximum Junction-to-Foot (Drain)		$R_{thJF}$	15	20	

**Notes**

- Surface Mounted on 1" x 1" FR4 Board.
- See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

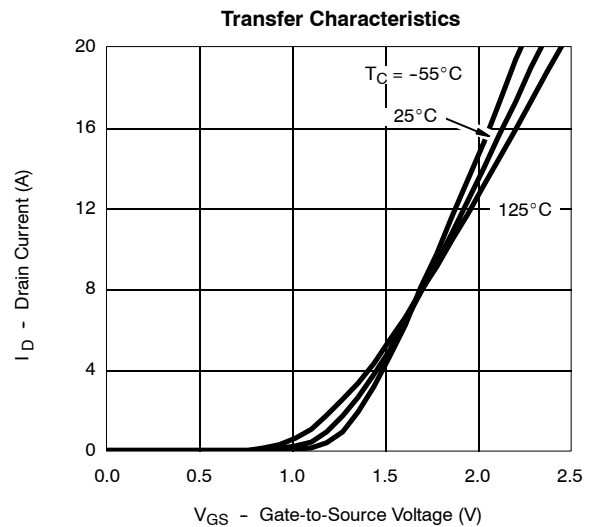
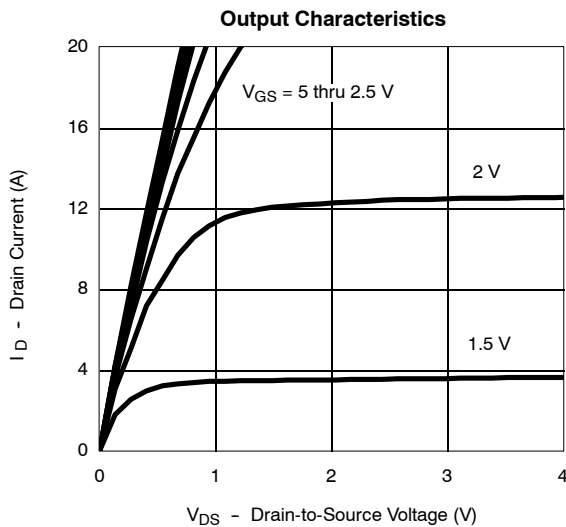


SPECIFICATIONS (T <sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-0.45			V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±8 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -16 V, V <sub>GS</sub> = 0 V			-1	μA
		V <sub>DS</sub> = -16 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C			-5	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≤ -5 V, V <sub>GS</sub> = -4.5 V	-20			A
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -4.8 A		0.036	0.040	Ω
		V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -4.2 A		0.045	0.052	
		V <sub>GS</sub> = -1.8 V, I <sub>D</sub> = -1 A		0.062	0.072	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -4.8 A		15		S
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = -1.1 A, V <sub>GS</sub> = 0 V		-0.8	-1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -4.8 A		15	22	nC
Gate-Source Charge	Q <sub>gs</sub>			3.6		
Gate-Drain Charge	Q <sub>gd</sub>			2.5		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = -10 V, R <sub>L</sub> = 10 Ω I <sub>D</sub> ≅ -1 A, V <sub>GEN</sub> = -4.5 V, R <sub>G</sub> = 6 Ω		22	35	ns
Rise Time	t <sub>r</sub>			29	45	
Turn-Off Delay Time	t <sub>d(off)</sub>			94	140	
Fall Time	t <sub>f</sub>			54	80	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>		I <sub>F</sub> = -1.1 A, di/dt = 100 A/μs		30	

Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

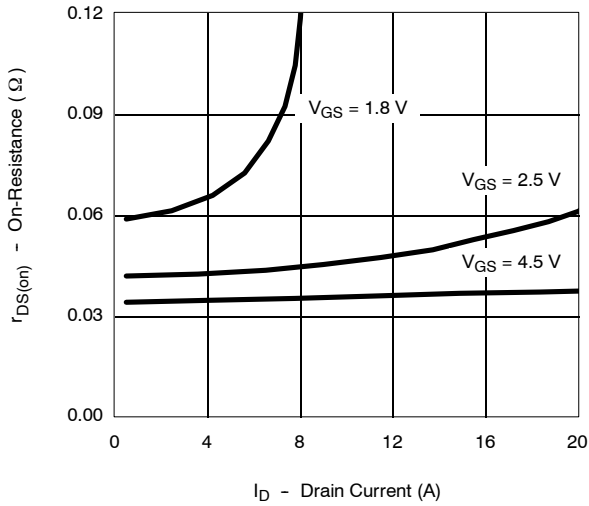
**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**



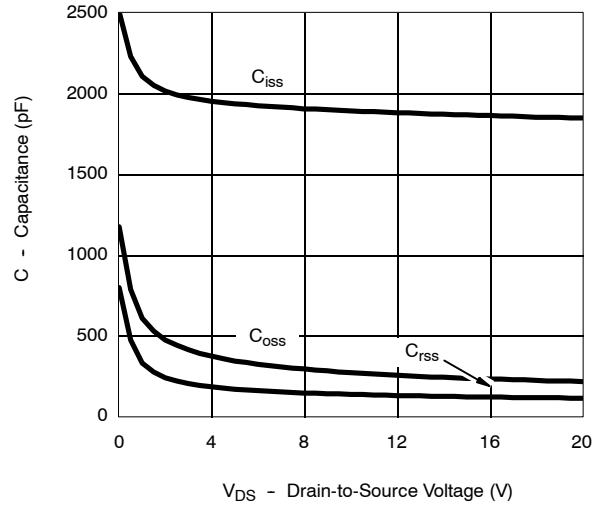


**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

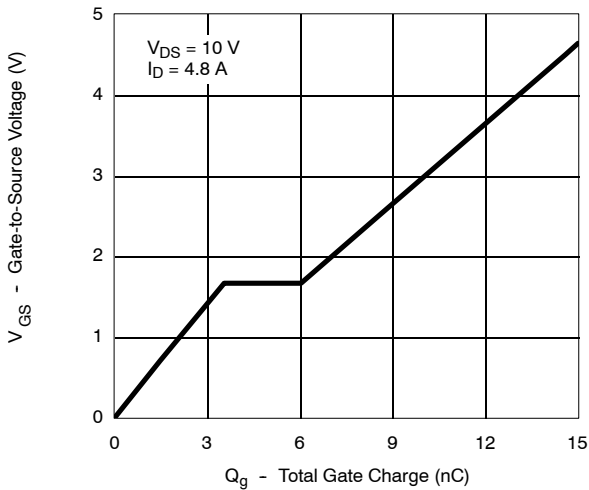
**On-Resistance vs. Drain Current**



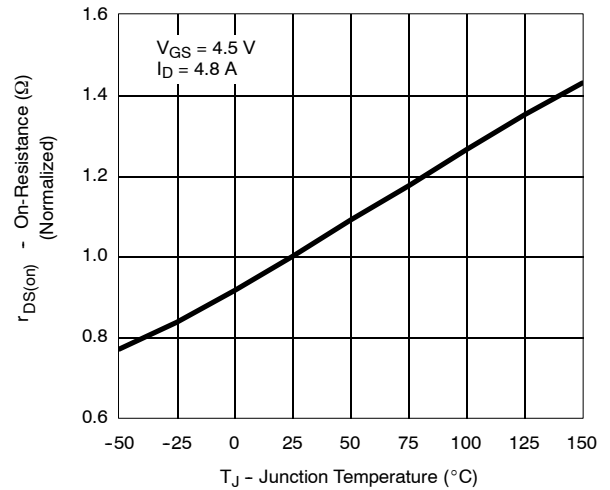
**Capacitance**



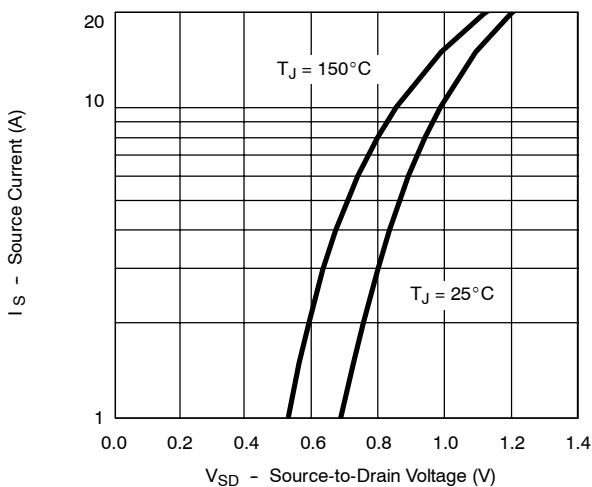
**Gate Charge**



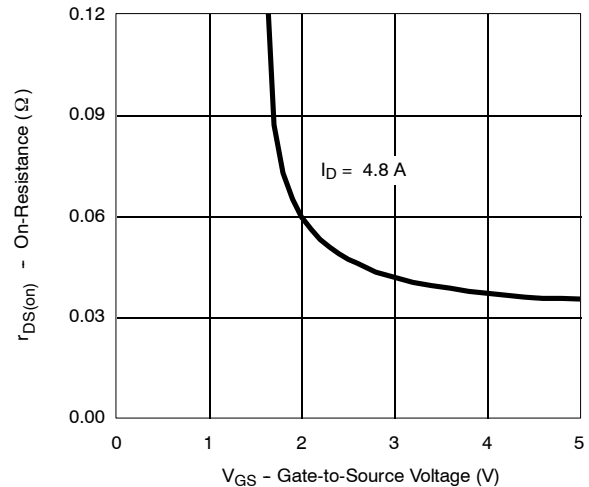
**On-Resistance vs. Junction Temperature**



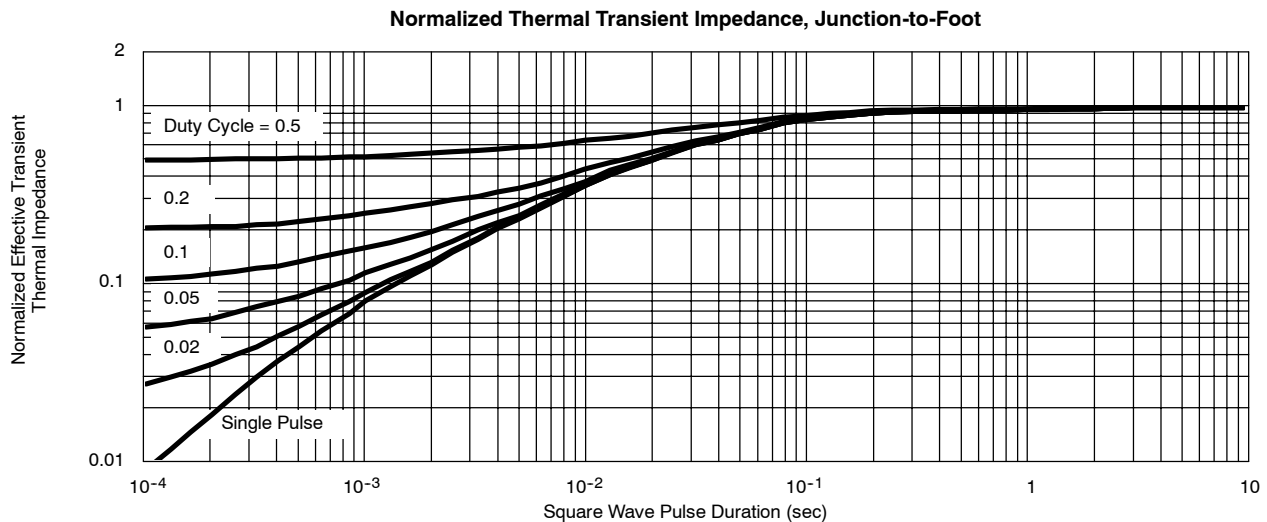
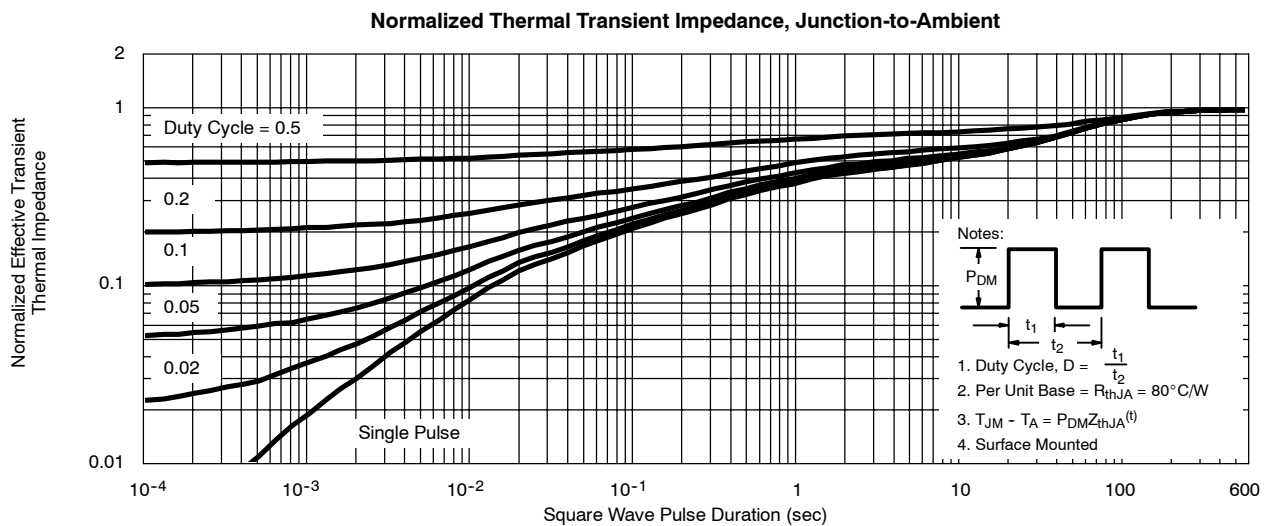
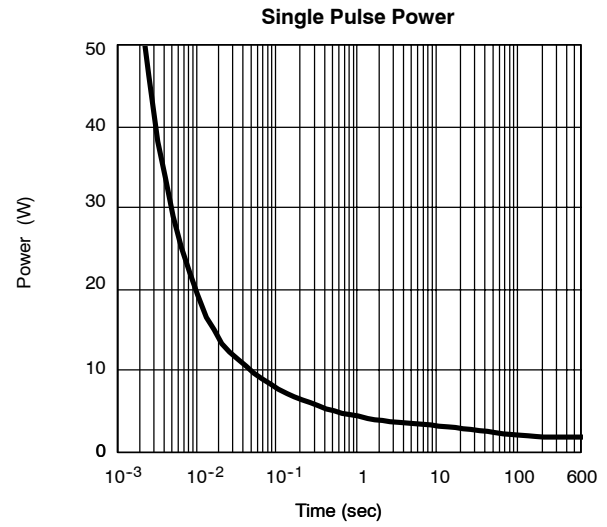
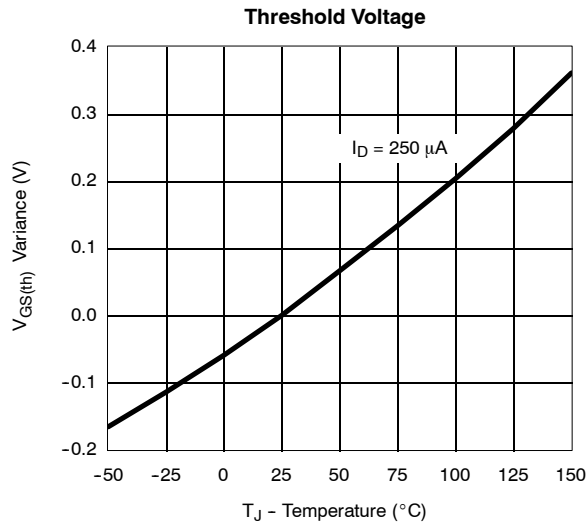
**Source-Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**





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